



Product Overview

Created on: 10/26/2011

NSS35200CF8T1G: 35 V, 2.0 A PNP Low $V_{CE(sat)}$ Bipolar Transistor

For complete documentation, see the data sheet

Product Description

Low $V_{CE(sat)}$ Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage $V_{CE(sat)}$ and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Features

- Very Low Saturation
- High Current Switching 2A DC, 7A Peak
- High Current Gain
- High Cut Off Frequency
- Low Profile Package
- Linear Gain (Beta)
- This is a Pb-Free Device

Applications

- DC/DC Converter
- Complimentary Driver
- Supply line Load Switch
- Current Extention & Low Drop Out Regulation
- Battery Charging, Linear & Pulsed

Part Electrical Specifications

Product	Compliance	Status	I_C Max (A)	$V_{(BR)/CEO}$ Min (V)	$V_{CE(sat)}$ Max (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Polarity	Package Type
NSS35200CF8T1G	Pb-free Halide free	Active	7	35	0.1	100	400	100	2.75	PNP	ChipFET-8

Package Availability

Type	Pb-free	Standard
ChipFET-8	✓	

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